

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): A gallium nitride-based semiconductor device having a p-type layer that is a gallium nitride compound semiconductor layer containing a p-type impurity and exhibiting p-type conduction, wherein the p-type layer comprises a top portion and an inner portion located under the top portion and wherein the inner portion contains the p-type impurity element and, in combination therewith, hydrogen.
2. (original): A gallium nitride-based semiconductor device according to claim 1, wherein the p-type impurity is incorporated in the p-type layer by means of doping or ion injection.
3. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~or claim 2~~, wherein the inner portion of the p-type layer has a ratio of atomic concentration of the hydrogen to that of the p-type impurity of about 1:1.
4. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~or claim 2~~, wherein the inner portion of the p-type layer has a percent thickness of 40% to 99.9% with respect to a total thickness of the p-type layer.

5. (original): A gallium nitride-based semiconductor device according to claim 4, wherein the inner portion of the p-type layer has a percent thickness of 70% or more with respect to the total thickness of the p-type layer.

6. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~any one of claims 1 to 5~~, wherein the top portion of the p-type layer has a hydrogen content that is 1/3 or less the amount of the hydrogen contained in the inner portion.

7. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~any one of claims 1 to 5~~, wherein the top portion of the p-type layer has a hydrogen content that is 1/2 or less the amount of the hydrogen contained in the inner portion.

8. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~any one of claims 1 to 5~~, wherein the top portion of the p-type layer has a hydrogen content that is 2/3 or less the amount of tale hydrogen contained in the inner portion.

9. (currently amended): A gallium nitride-based semiconductor device according to claim 1 ~~any one of claims 1 to 5~~, wherein the top portion of the p-type layer has a hydrogen content that is less than the amount of the hydrogen contained in the inner portion.